

Day 5-7-02 P3
Pre-Amendment
PATENT
3885-0103P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: ONO, Yoshinobu et al Conf.:
Appl. No.: NEW Group:
Filed: January 17, 2002 Examiner:
For: METHOD FOR FABRICATING III-V COMPOUND SEMICONDUCTOR

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, DC 20231

January 17, 2002

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amend the claims as follows:

A1
4. (Amended) A method for fabricating a III-V Group compound semiconductor as claimed in claim 1, further comprising a step of forming on the second layer by epitaxial growth at least one $Al_{y_j}Ga_{1-y_j}$ As layer ($0 \leq y_j < 1$, $j=1, 2, \dots$).